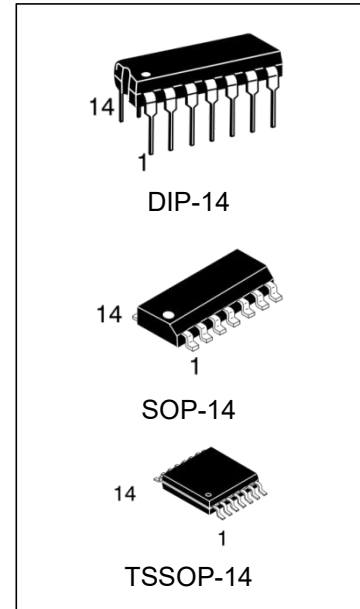


CD4066 Quad Bilateral Switches

Features:

- Wide supply voltage range from 3V to 9V
- Fully static operation
- 5V and 9V parametric ratings
- Standardized symmetrical output characteristics
- Inputs and outputs are protected against electrostatic effects
- Specified from -40°C to +85°C
- Packaging information: DIP14/SOP14/TSSOP14



Ordering Information

| DEVICE | Package Type | MARKING | Packing | Packing Qty |
|-----------------------|--------------|---------|---------|--------------|
| CD4066BE/ CD4066BN | DIP-14 | CD4066B | TUBE | 1000pcs/box |
| CD4066BM/TR | SOP-14 | CD4066B | REEL | 2500pcs/reel |
| CD4066BMT/TR | TSSOP-14 | CD4066B | REEL | 2500pcs/reel |

General Description

The CD4066B provides four single-pole, single-throw analog switch functions. Each switch has two input/output terminals (nY and nZ) and an active HIGH enable input (nE). When nE is LOW, the analog switch is turned off.

Block Diagram

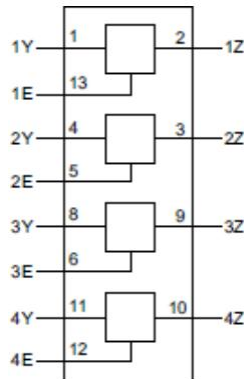


Figure 1. Functional diagram

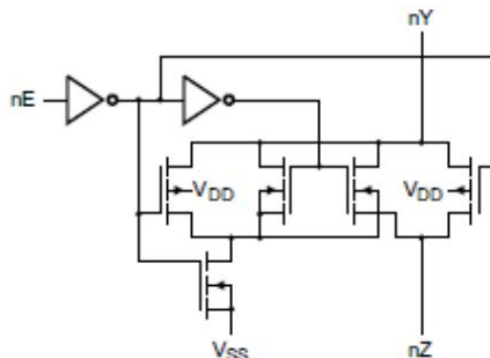


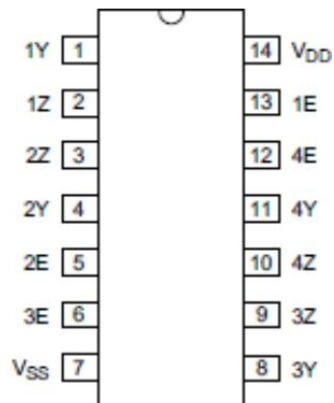
Figure 2. Logic diagram (one switch)

Function Table

| Input | Switch |
|-------|--------|
| nE | |
| H | ON |
| L | OFF |

Note: H=HIGH voltage level; L=LOW voltage level.

Pin Configurations



DIP-14/SOP-14/TSSOP-14

Pin Description

| Pin No. | Pin Name | Description |
|---------|-----------------|-----------------------------|
| 1 | 1Y | independent input or output |
| 2 | 1Z | independent input or output |
| 3 | 2Z | independent input or output |
| 4 | 2Y | independent input or output |
| 5 | 2E | enable input (active HIGH) |
| 6 | 3E | enable input (active HIGH) |
| 7 | V _{SS} | ground (0V) |
| 8 | 3Y | independent input or output |
| 9 | 3Z | independent input or output |
| 10 | 4Z | independent input or output |
| 11 | 4Y | independent input or output |
| 12 | 4E | enable input (active HIGH) |
| 13 | 1E | enable input (active HIGH) |
| 14 | V _{DD} | supply voltage |

Absolute Maximum Ratings

(Voltages are referenced to V_{SS} (ground=0V), unless otherwise specified.)

| Parameter | Symbol | Conditions | Min. | Max. | Unit |
|-------------------------|-----------|---------------------------------------|------|--------------|------|
| supply voltage | V_{DD} | - | -0.5 | +12 | V |
| input voltage | V_I | - | -0.5 | $V_{DD}+0.5$ | V |
| input clamping current | I_{IK} | $V_I < 0.5V$ or $V_I > V_{DD} + 0.5V$ | - | ± 10 | mA |
| input/output current | $I_{I/O}$ | - | - | ± 10 | mA |
| storage temperature | T_{stg} | - | -65 | +150 | °C |
| total power dissipation | P_{tot} | - | - | 500 | mW |
| device dissipation | P | per output transistor | - | 100 | mW |
| Soldering temperature | T_L | 10s | DIP | 245 | °C |
| | | | SOP | | °C |

- Note:**
- 1、 Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured.
 - 2、 For DIP14 packages: above 70°C the value of P_{tot} derates linearly with 12mW/K.
 - 3、 For SOP14 packages: above 70°C the value of P_{tot} derates linearly with 8mW/K.
 - 4、 For (T)SSOP14 packages: above 60°C the value of P_{tot} derates linearly with 5.5mW/K.

Recommended Operating Conditions

($T_{amb}=25^\circ\text{C}$; $R_L=10\text{k}\Omega$; $C_L=50\text{pF}$; $nE=V_{DD}$; $V_{is}=V_{DD}=5V$.)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|--------------------|----------------------|------|------|----------|------|
| supply voltage | V_{DD} | - | 3 | 5 | 9 | V |
| ambient temperature | T_{amb} | in free air | -40 | - | +85 | °C |
| input voltage | V_I | - | 0 | - | V_{DD} | V |
| Disable output time (High level→turn off) | t_{PHZ} | nE to nZ or nE to nY | - | 80 | 160 | ns |
| Disable output time (Low level→turn off) | t_{PLZ} | nE to nZ or nE to nY | - | 80 | 160 | ns |
| Enable output time (turn off→high/low level) | t_{PZH}, t_{PZL} | - | - | 45 | 90 | ns |
| input capacitance | C_I | - | - | - | 7.5 | pF |

Electrical Characteristics

DC Characteristics 1

($T_{amb}=25^{\circ}\text{C}$, voltages are referenced to V_{SS} (ground=0V), unless otherwise specified.)

| Parameter | Symbol | Conditions (V) | | $T_{amb}=25^{\circ}\text{C}$ | | | Unit |
|---|-----------------|---|--|------------------------------|------|------|---------------|
| | | | | Min. | Typ. | Max. | |
| supply current | I_{DD} | $V_I=V_{DD}$ or V_{SS} , $I_O=0\text{A}$ | $V_{DD}=5\text{V}$ | - | - | 1.0 | μA |
| | | | $V_{DD}=9\text{V}$ | - | - | 2.0 | μA |
| HIGH-level input voltage | V_{IH} | $ I_O <1\mu\text{A}$ | $V_{DD}=5\text{V}$, $V_O=0.5\text{V}$ or 4.5V | 3.5 | - | - | V |
| | | | $V_{DD}=9\text{V}$, $V_O=0.5\text{V}$ or 8V | 7.0 | - | - | V |
| LOW-level input voltage | V_{IL} | $ I_O <1\mu\text{A}$ | $V_{DD}=5\text{V}$, $V_O=0.5\text{V}$ or 4.5V | - | - | 1.5 | V |
| | | | $V_{DD}=9\text{V}$, $V_O=0.5\text{V}$ or 8V | - | - | 3.0 | V |
| input leakage current | I_i | $V_I=0\text{V}$ or 9V , $V_{DD}=9\text{V}$ | | - | - | 0.3 | μA |
| ON resistance (rail) | R_{ON} | $V_I=0\text{V}$ to $V_{DD}-V_{EE}$ | $V_{DD}-V_{EE}=5\text{V}$ | - | 350 | 2500 | Ω |
| | | | $V_{DD}-V_{EE}=9\text{V}$ | - | 80 | 245 | Ω |
| | | $V_I=0\text{V}$ | $V_{DD}-V_{EE}=5\text{V}$ | - | 115 | 340 | Ω |
| | | | $V_{DD}-V_{EE}=9\text{V}$ | - | 50 | 160 | Ω |
| | | $V_I=V_{DD}-V_{EE}$ | $V_{DD}-V_{EE}=5\text{V}$ | - | 120 | 365 | Ω |
| | | | $V_{DD}-V_{EE}=9\text{V}$ | - | 65 | 200 | Ω |
| ON resistance mismatch between channels | ΔR_{ON} | $V_I=0\text{V}$ to $V_{DD}-V_{EE}$ | $V_{DD}-V_{EE}=5\text{V}$ | - | 25 | - | Ω |
| | | | $V_{DD}-V_{EE}=9\text{V}$ | - | 10 | - | Ω |

Note: On resistance waveform and test circuit see Figure 9 and Figure 10.

DC Characteristics 2

($T_{amb} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, voltages are referenced to V_{SS} (ground=0V), unless otherwise specified.)

| Parameter | Symbol | Conditions (V) | $T_{amb} = -40^{\circ}\text{C}$ | | $T_{amb} = +85^{\circ}\text{C}$ | | Unit | |
|--------------------------|----------|---|--|------|---------------------------------|------|---------------|---------------|
| | | | Min. | Max. | Min. | Max. | | |
| supply current | I_{DD} | $V_i = V_{DD}$ or V_{SS} , $I_o = 0\text{A}$ | $V_{DD} = 5\text{V}$ | - | 1.0 | - | 7.5 | μA |
| | | | $V_{DD} = 9\text{V}$ | - | 2.0 | - | 15.0 | μA |
| HIGH-level input voltage | V_{IH} | $ I_o < 1\mu\text{A}$ | $V_{DD} = 5\text{V}$, $V_o = 0.5\text{V}$ or 4.5V | 3.5 | - | 3.5 | - | V |
| | | | $V_{DD} = 9\text{V}$, $V_o = 0.5\text{V}$ or 8V | 7.0 | - | 7.0 | - | V |
| LOW-level input voltage | V_{IL} | $ I_o < 1\mu\text{A}$ | $V_{DD} = 5\text{V}$, $V_o = 0.5\text{V}$ or 4.5V | - | 1.5 | - | 1.5 | V |
| | | | $V_{DD} = 9\text{V}$, $V_o = 0.5\text{V}$ or 8V | - | 3.0 | - | 3.0 | V |
| input leakage current | I_i | $V_i = 0\text{V}$ or 9V , $V_{DD} = 9\text{V}$ | - | - | - | 1.0 | μA | |

AC Characteristics 1

($T_{amb} = 25^{\circ}\text{C}$, $V_{EE} = V_{SS} = 0\text{V}$, $t_r, t_f \leq 20\text{ns}$, $C_L = 50\text{pF}$, $R_L = 10\text{k}\Omega$, unless otherwise specified.)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit | |
|-------------------------------------|-----------|-------------------------------------|----------------------|------|------|------|----|
| HIGH to LOW propagation delay time | t_{PHL} | nY to nZ; nZ to nY; see Figure 4 | $V_{DD} = 5\text{V}$ | - | 10 | 20 | ns |
| | | | $V_{DD} = 9\text{V}$ | - | 5 | 10 | ns |
| LOW to HIGH propagation delay | t_{PLH} | nY to nZ; nZ to nY; see Figure 4 | $V_{DD} = 5\text{V}$ | - | 10 | 20 | ns |
| | | | $V_{DD} = 9\text{V}$ | - | 5 | 10 | ns |
| HIGH to OFF-state propagation delay | t_{PHZ} | nE to nY, nZ; see Figure 5 | $V_{DD} = 5\text{V}$ | - | 80 | 160 | ns |
| | | | $V_{DD} = 9\text{V}$ | - | 65 | 130 | ns |
| LOW to OFF-state propagation delay | t_{PLZ} | nE to nY, nZ; see Figure 5 | $V_{DD} = 5\text{V}$ | - | 80 | 160 | ns |
| | | | $V_{DD} = 9\text{V}$ | - | 70 | 140 | ns |
| OFF-state to HIGH propagation delay | t_{PZH} | nE to nY, nZ; see Figure 5 | $V_{DD} = 5\text{V}$ | - | 40 | 80 | ns |
| | | | $V_{DD} = 9\text{V}$ | - | 20 | 40 | ns |
| OFF-state to LOW propagation delay | t_{PZL} | nE to nY, nZ; see Figure 5 | $V_{DD} = 5\text{V}$ | - | 45 | 90 | ns |
| | | | $V_{DD} = 9\text{V}$ | - | 20 | 40 | ns |

AC Characteristics 2

($T_{amb}=25^{\circ}C$, $V_{EE}=V_{SS}=0V$, $V_i=0.5V_{DD}$ (p-p), unless otherwise specified.)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Unit | |
|------------------------------------|-----------|---|-------------|------|------|------|---|
| Square wave distortion | d_{sin} | see Figure 6; $R_L=10k\Omega$; $C_L=15pF$; channel ON; $f_i=1kHz$ | $V_{DD}=5V$ | 0.25 | - | - | % |
| | | | $V_{DD}=9V$ | 0.04 | - | - | % |
| any two channel crosstalk | f_{ct} | $V_{DD}=9V$, see note2 | 1 | - | - | MHz | |
| crosstalk voltage (nE to nY to nZ) | V_{ct} | see Figure 7; $R_L=10k\Omega$; $C_L=15pF$; \bar{E} or Sn= V_{DD} (square-wave) | 50 | - | - | mV | |
| OFF frequency | f_{OFF} | $V_{DD}=9V$, see note3 | 1 | - | - | MHz | |
| conduction frequency | f_{ON} | $V_{DD}=5V$, see note4 | - | - | - | MHz | |
| | | $V_{DD}=9V$, see note4 | 90 | - | - | MHz | |

Note:

- (1) f_i is biased at $0.5V_{DD}$; $V_i=0.5V_{DD}$ (p-p).
- (2) $R_L=1k\Omega$; $20\log V_{os}/V_{is}=-50dB$, see Figure 8.
- (3) $R_L=1k\Omega$; $C_L=5pF$, channel off, $20\log V_{os}/V_{is}=-50dB$, see Figure 6.
- (4) $R_L=1k\Omega$; $C_L=5pF$, channel on, $20\log V_{os}/V_{is}=-3dB$, see Figure 6.

Testing Circuit

AC Testing Circuit 1

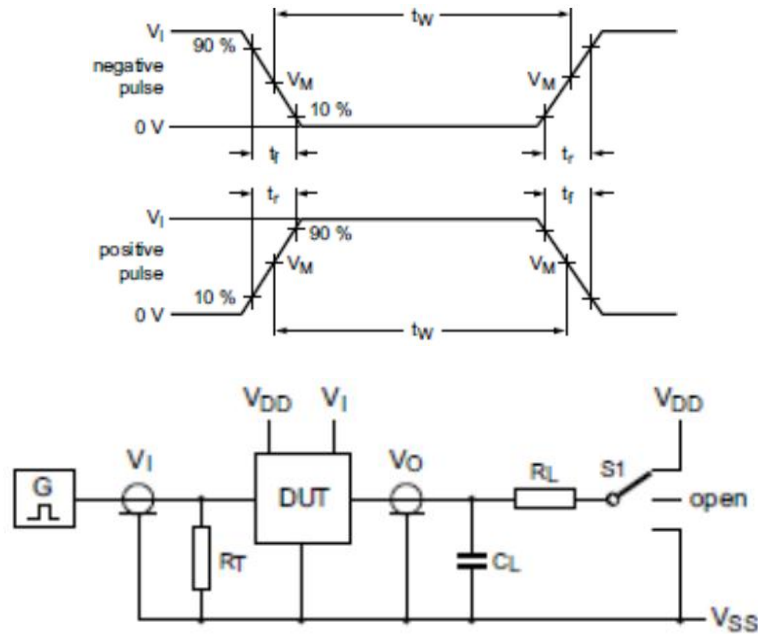


Figure 3. Test circuit for switching times

Definitions for test circuit:

DUT=Device Under Test.

C_L =Load capacitance including jig and probe capacitance.

R_T =Termination resistance should be equal to the output impedance Z_o of the pulse generator.

R_L =Load resistance.

AC Testing Waveforms

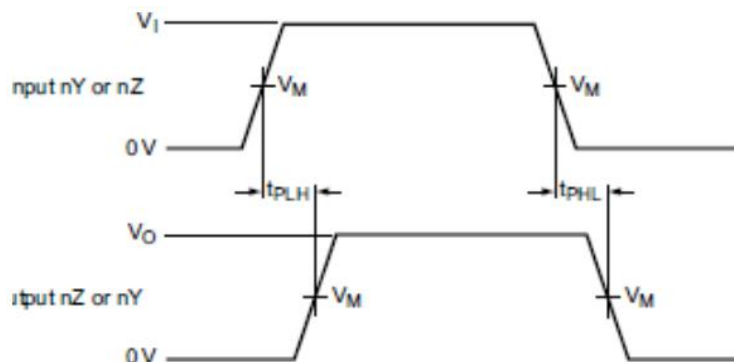


Figure 4. nY or nZ to nZ or nY propagation delays

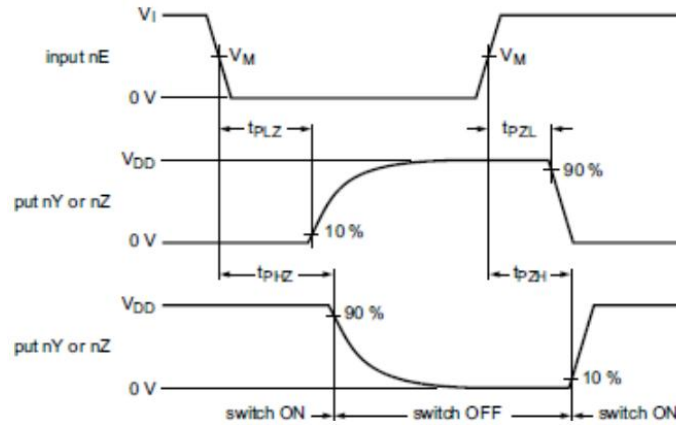


Figure 5. Enable and disable times

AC Testing Circuit 2

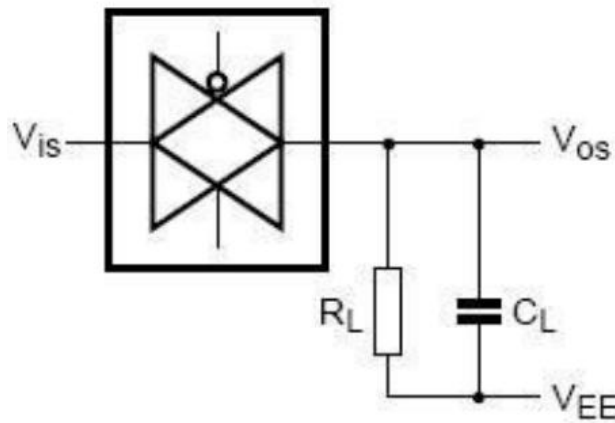


Figure 6. Square wave distortion degree of cut-off frequency and conduction frequency test pattern

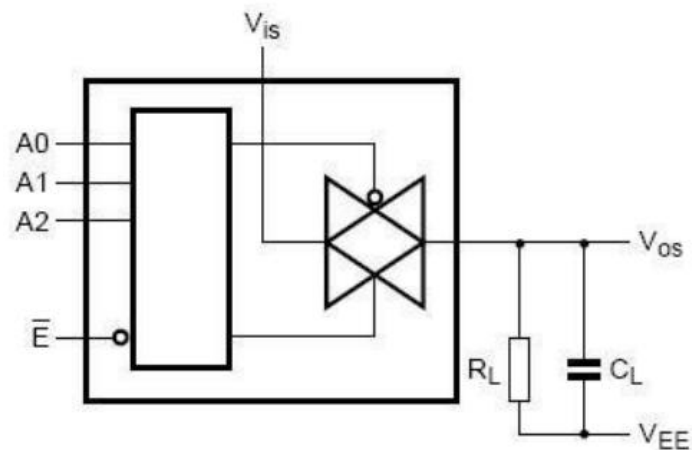


Figure 7. Crosstalk logical input/output test

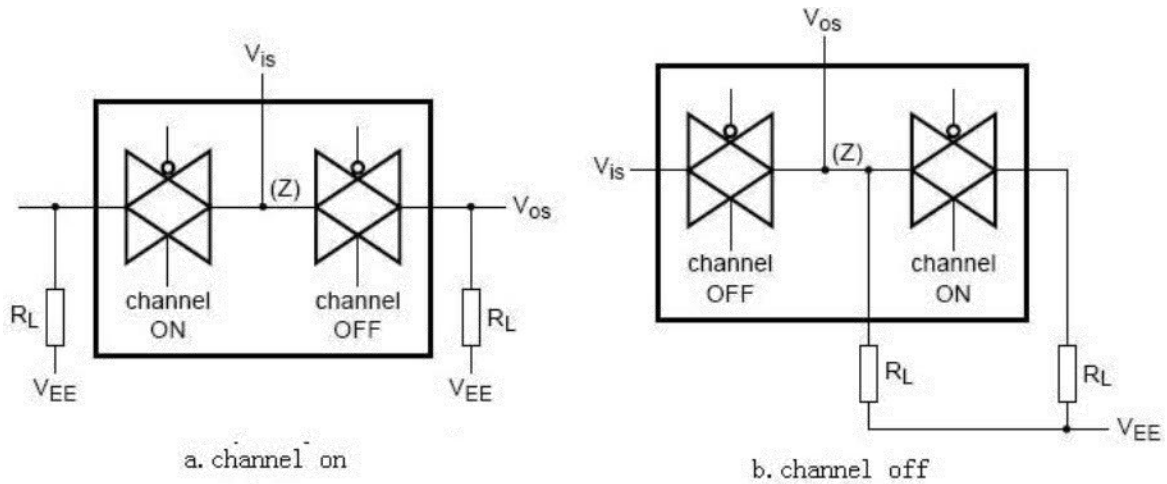
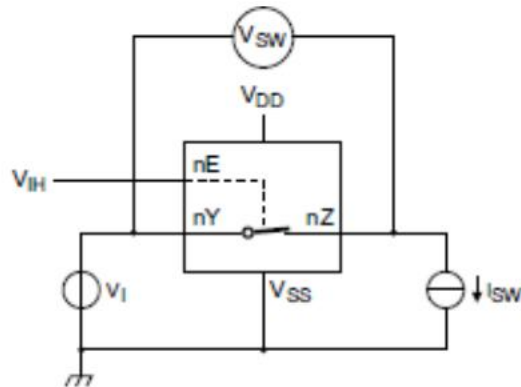


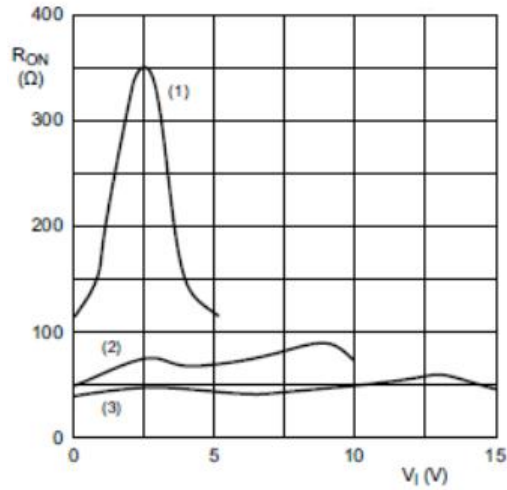
Figure 8. Inter channel Crosstalk

On Resistance Waveform And Test Circuit



$$R_{ON} = V_{SW} / I_{SW}$$

Figure 9. Test circuit for measuring R_{ON}



$I_{SW} = 200 \mu A.$
 (1) $V_{DD} = 5 V$
 (2) $V_{DD} = 10 V$
 (3) $V_{DD} = 15 V$

Figure 10. Typical R_{ON} as a function of input voltage

Measurement Points

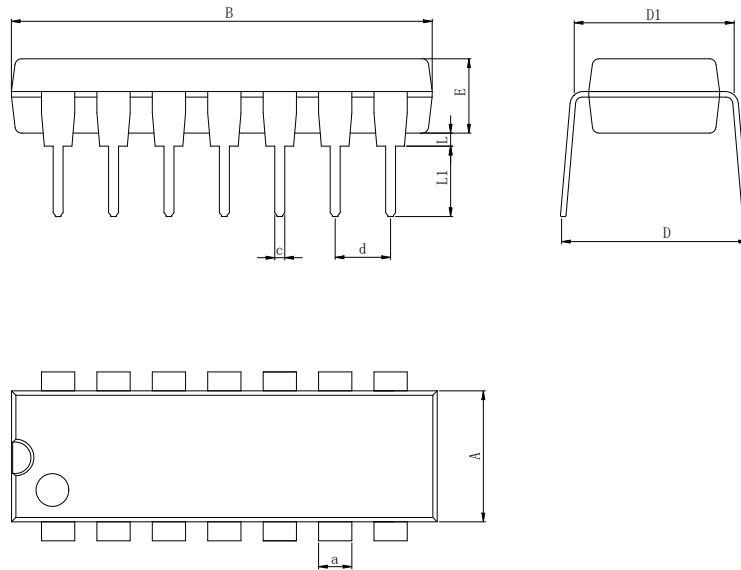
| Supply voltage | Input | Output |
|----------------|---------------------|---------------------|
| V_{DD} | V_M | V_M |
| 3V to 9V | $0.5 \times V_{DD}$ | $0.5 \times V_{DD}$ |

Test Data

| Test | Input | | Load | | Switch |
|--------------------|----------|------------|-------|-------|----------|
| | V_{is} | t_r, t_f | C_L | R_L | |
| t_{PHL} | V_{EE} | 20ns | 50pF | 10kΩ | V_{DD} |
| t_{PLH} | V_{DD} | 20ns | 50pF | 10kΩ | V_{EE} |
| t_{PZH}, t_{PHZ} | V_{DD} | 20ns | 50pF | 10kΩ | V_{EE} |
| t_{PZL}, t_{PLZ} | V_{EE} | 20ns | 50pF | 10kΩ | V_{DD} |
| others | pulse | 20ns | 50pF | 10kΩ | open |

Physical Dimensions

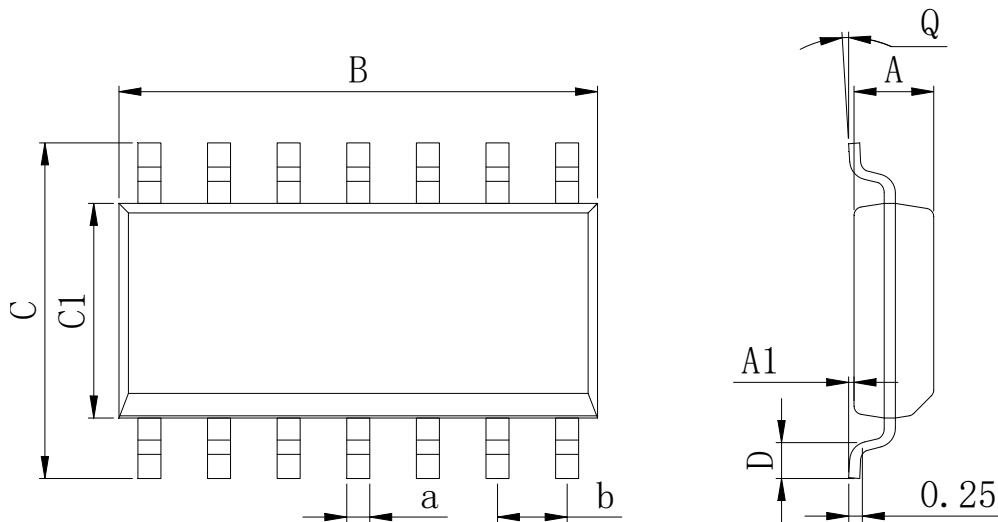
DIP-14



Dimensions In Millimeters(DIP-14)

| Symbol: | A | B | D | D1 | E | L | L1 | a | c | d |
|---------|------|-------|------|------|------|------|------|------|------|----------|
| Min: | 6.10 | 18.94 | 8.10 | 7.42 | 3.10 | 0.50 | 3.00 | 1.50 | 0.40 | 2.54 BSC |
| Max: | 6.68 | 19.56 | 10.9 | 7.82 | 3.55 | 0.70 | 3.60 | 1.55 | 0.50 | |

SOP-14

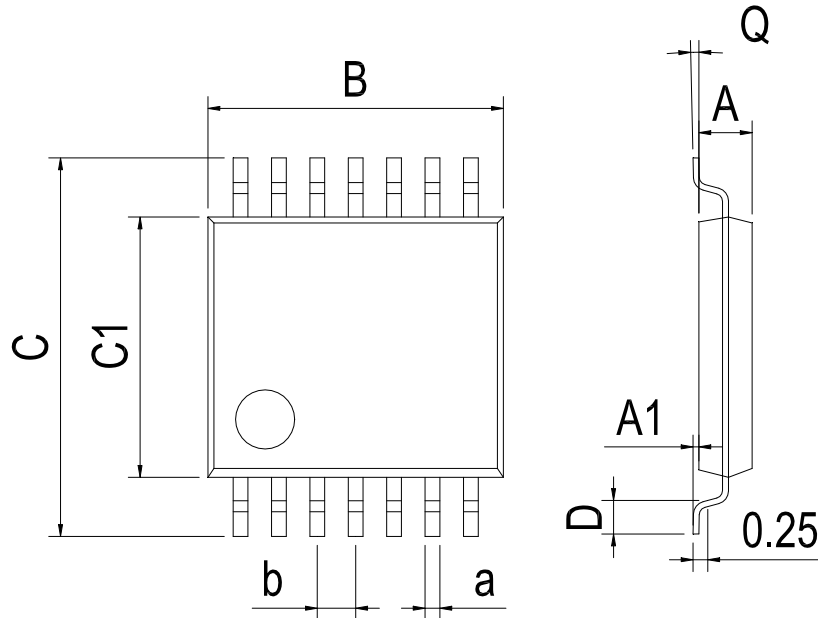


Dimensions In Millimeters(SOP-14)

| Symbol: | A | A1 | B | C | C1 | D | Q | a | b |
|---------|------|------|------|------|------|------|----|------|----------|
| Min: | 1.35 | 0.05 | 8.55 | 5.80 | 3.80 | 0.40 | 0° | 0.35 | 1.27 BSC |
| Max: | 1.55 | 0.20 | 8.75 | 6.20 | 4.00 | 0.80 | 8° | 0.45 | |

Physical Dimensions

TSSOP-14



| Dimensions In Millimeters(TSSOP-14) | | | | | | | | | |
|-------------------------------------|------|------|------|------|------|------|----|------|----------|
| Symbol: | A | A1 | B | C | C1 | D | Q | a | b |
| Min: | 0.85 | 0.05 | 4.90 | 6.20 | 4.30 | 0.40 | 0° | 0.20 | 0.65 BSC |
| Max: | 0.95 | 0.20 | 5.10 | 6.60 | 4.50 | 0.80 | 8° | 0.25 | |

Revision History

| DATE | REVISION | PAGE |
|------------|---|---------|
| 2015-5-28 | New | 1-15 |
| 2023-11-14 | Document Reformatting、 Update DIP Package New Model | 1-15、 1 |

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